

isc Silicon NPN Power Transistor

2SC3371

DESCRIPTION

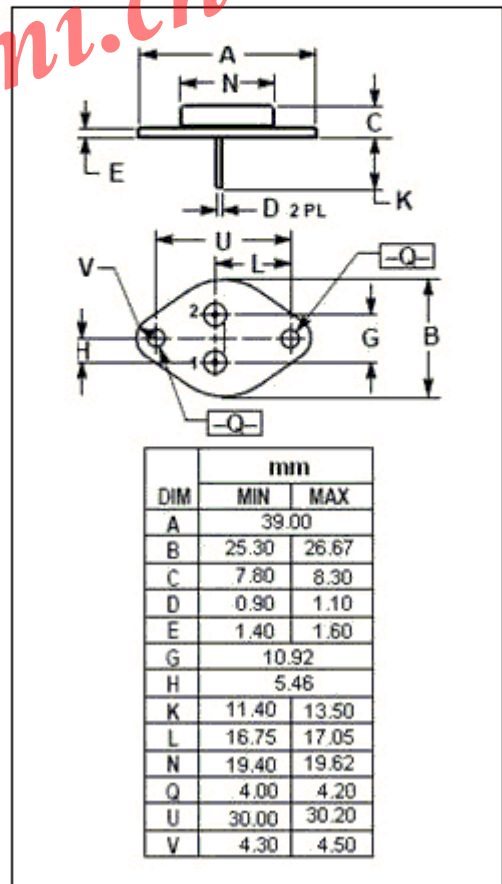
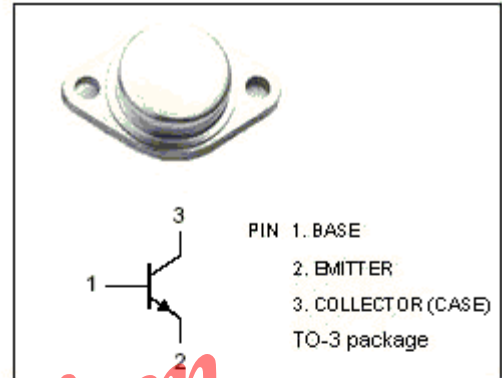
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 500V(\text{Min.})$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 1.0V(\text{Max.}) @ I_C = 8A$
- High Speed Switching

APPLICATIONS

- Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	800	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	200	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor

2SC3371

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 0.5A; L= 25mH	500			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			0.1	mA
h _{FE-1}	DC Current Gain	I _C = 0.1A; V _{CE} = 5V	15			
h _{FE-2}	DC Current Gain	I _C = 8A; V _{CE} = 5V	10			

Switching Times; Resistive Load

t _{on}	Turn-on Time	I _C = 8A; I _{B1} = -I _{B2} = 1.6A; V _{CC} = 200V			1.0	μs
t _s	Storage Time				3.0	μs
t _f	Fall Time				1.0	μs